

# MOSFET

## 800V CoolMOS™ P7 Power Device

The latest 800V CoolMOS™ P7 series sets a new benchmark in 800V super junction technologies and combines best-in-class performance with state of the art ease-of-use, resulting from Infineon's over 18 years pioneering super junction technology innovation.

### Features

- Best-in-class FOM  $R_{DS(on)} * E_{oss}$ ; reduced  $Q_g$ ,  $C_{iss}$ , and  $C_{oss}$
- Best-in-class DPAK  $R_{DS(on)}$
- Best-in-class  $V_{GS(th)}$  of 3V and smallest  $V_{GS(th)}$  variation of  $\pm 0.5V$
- Integrated Zener Diode ESD protection
- Fully optimized portfolio

### Benefits

- Best-in-class performance
- Enabling higher power density designs, BOM savings and lower assembly costs
- Easy to drive and to parallel
- Better production yield by reducing ESD related failures
- Less production issues and reduced field returns
- Easy to select right parts for fine tuning of designs

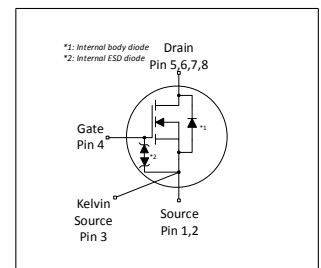
### Potential applications

Recommended for hard and soft switching flyback topologies for low power Chargers and Adapters.

### Product validation

Fully qualified according to JEDEC for Industrial Applications

*Please note: The source and sense source pins are not exchangeable. Their exchange might lead to malfunction. For paralleling 4pin MOSFET devices the placement of the gate resistor is generally recommended to be on the Driver Source instead of the Gate.*



RoHS

**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS} @ T_J=25^{\circ}C$	800	V
$R_{DS(on),max}$	0.90	$\Omega$
$Q_{g,typ}$	15	nC
$I_D$	6	A
$E_{oss} @ 500V$	1.4	$\mu J$
$V_{GS(th),typ}$	3	V
ESD class (HBM)	2	-

Type / Ordering Code	Package	Marking	Related Links
IPLK80R900P7	ThinPAK 5x6 SMD	80R900P7	see Appendix A

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## 1 Maximum ratings

at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current <sup>1)</sup>	$I_D$	-	-	6 3.9	A	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	-	-	14	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	$E_{AS}$	-	-	13	mJ	$I_D=0.9\text{A}$ ; $V_{DD}=50\text{V}$
Avalanche energy, repetitive	$E_{AR}$	-	-	0.11	mJ	$I_D=0.9\text{A}$ ; $V_{DD}=50\text{V}$
Avalanche current, repetitive	$I_{AR}$	-	-	0.9	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	100	V/ns	$V_{DS}=0$ to 400V
Gate source voltage	$V_{GS}$	-20 -30	-	20 30	V	static; AC ( $f>1$ Hz)
Power dissipation	$P_{tot}$	-	-	54	W	$T_C=25^\circ\text{C}$
Operating and storage temperature	$T_j, T_{stg}$	-55	-	150	$^\circ\text{C}$	-
Continuous diode forward current	$I_S$	-	-	4.8	A	$T_C=25^\circ\text{C}$
Diode pulse current <sup>2)</sup>	$I_{S,pulse}$	-	-	14	A	$T_C=25^\circ\text{C}$
Reverse diode dv/dt <sup>3)</sup>	dv/dt	-	-	1	V/ns	$V_{DS}=0$ to 400V, $I_{SD}<=1.1\text{A}$ , $T_j=25^\circ\text{C}$
Maximum diode commutation speed <sup>3)</sup>	di/dt	-	-	50	A/ $\mu\text{s}$	$V_{DS}=0$ to 400V, $I_{SD}<=1.1\text{A}$ , $T_j=25^\circ\text{C}$

## 2 Thermal characteristics

**Table 3 Thermal characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$	-	-	2.3	$^\circ\text{C/W}$	-
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	62	$^\circ\text{C/W}$	Device on PCB, minimal footprint
Thermal resistance, junction - ambient for SMD version	$R_{thJA}$	-	35	45	$^\circ\text{C/W}$	Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm <sup>2</sup> (one layer 70 $\mu\text{m}$ thickness) copper area for drain connection and cooling. PCB is vertical without airflow.
Soldering temperature, wave- & reflow soldering allowed	$T_{sold}$	-	-	260	$^\circ\text{C}$	reflow MSL1

<sup>1)</sup> Limited by  $T_{j,max}$ . Maximum duty cycle  $D=0.5$

<sup>2)</sup> Pulse width  $t_p$  limited by  $T_{j,max}$

<sup>3)</sup>  $V_{DClink}=400\text{V}$ ;  $V_{DS,peak}<V_{(BR)DSS}$ ; identical low side and high side switch with identical  $R_G$ ;  $t_{cond}<2\mu\text{s}$

### 3 Electrical characteristics

at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

**Table 4 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	800	-	-	V	$V_{GS}=0V, I_D=1mA$
Gate threshold voltage	$V_{GS(th)}$	2.5	3	3.5	V	$V_{DS}=V_{GS}, I_D=0.11mA$
Zero gate voltage drain current	$I_{DSS}$	-	-	1	$\mu A$	$V_{DS}=800V, V_{GS}=0V, T_j=25^\circ C$ $V_{DS}=800V, V_{GS}=0V, T_j=150^\circ C$
Gate-source leakage current incl. zener diode	$I_{GSS}$	-	-	1	$\mu A$	$V_{GS}=20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.77	0.90	$\Omega$	$V_{GS}=10V, I_D=2.2A, T_j=25^\circ C$ $V_{GS}=10V, I_D=2.2A, T_j=150^\circ C$
Gate resistance	$R_G$	-	1.4	-	$\Omega$	$f=250kHz, \text{open drain}$

**Table 5 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	$C_{iss}$	-	350	-	pF	$V_{GS}=0V, V_{DS}=500V, f=250kHz$
Output capacitance	$C_{oss}$	-	6	-	pF	$V_{GS}=0V, V_{DS}=500V, f=250kHz$
Effective output capacitance, energy related <sup>1)</sup>	$C_{o(er)}$	-	11	-	pF	$V_{GS}=0V, V_{DS}=0 \text{ to } 500V$
Effective output capacitance, time related <sup>2)</sup>	$C_{o(tr)}$	-	135	-	pF	$I_D=\text{constant}, V_{GS}=0V, V_{DS}=0 \text{ to } 500V$
Turn-on delay time	$t_{d(on)}$	-	12	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=2.2A, R_G=15\Omega$
Rise time	$t_r$	-	8	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=2.2A, R_G=15\Omega$
Turn-off delay time	$t_{d(off)}$	-	40	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=2.2A, R_G=15\Omega$
Fall time	$t_f$	-	20	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=2.2A, R_G=15\Omega$

**Table 6 Gate charge characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	$Q_{gs}$	-	2	-	nC	$V_{DD}=640V, I_D=2.2A, V_{GS}=0 \text{ to } 10V$
Gate to drain charge	$Q_{gd}$	-	6	-	nC	$V_{DD}=640V, I_D=2.2A, V_{GS}=0 \text{ to } 10V$
Gate charge total	$Q_g$	-	15	-	nC	$V_{DD}=640V, I_D=2.2A, V_{GS}=0 \text{ to } 10V$
Gate plateau voltage	$V_{plateau}$	-	4.5	-	V	$V_{DD}=640V, I_D=2.2A, V_{GS}=0 \text{ to } 10V$

<sup>1)</sup>  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 500V

<sup>2)</sup>  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 500V

**Table 7 Reverse diode characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	$V_{SD}$	-	0.9	-	V	$V_{GS}=0V, I_F=2.2A, T_i=25^{\circ}C$
Reverse recovery time	$t_{rr}$	-	840	-	ns	$V_R=400V, I_F=1.1A, di_F/dt=50A/\mu s$
Reverse recovery charge	$Q_{rr}$	-	6.2	-	$\mu C$	$V_R=400V, I_F=1.1A, di_F/dt=50A/\mu s$
Peak reverse recovery current	$I_{rrm}$	-	11	-	A	$V_R=400V, I_F=1.1A, di_F/dt=50A/\mu s$

## 4 Electrical characteristics diagrams

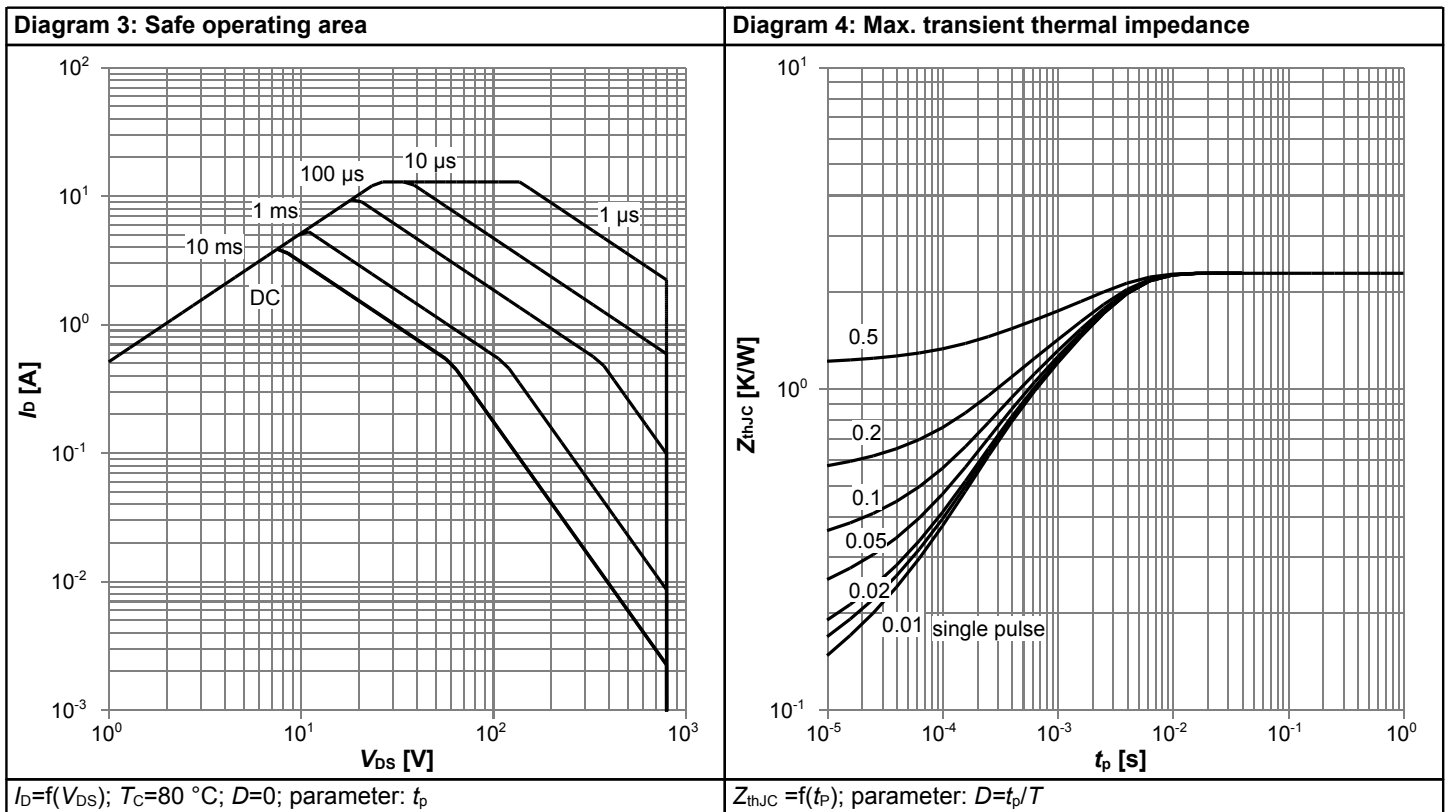
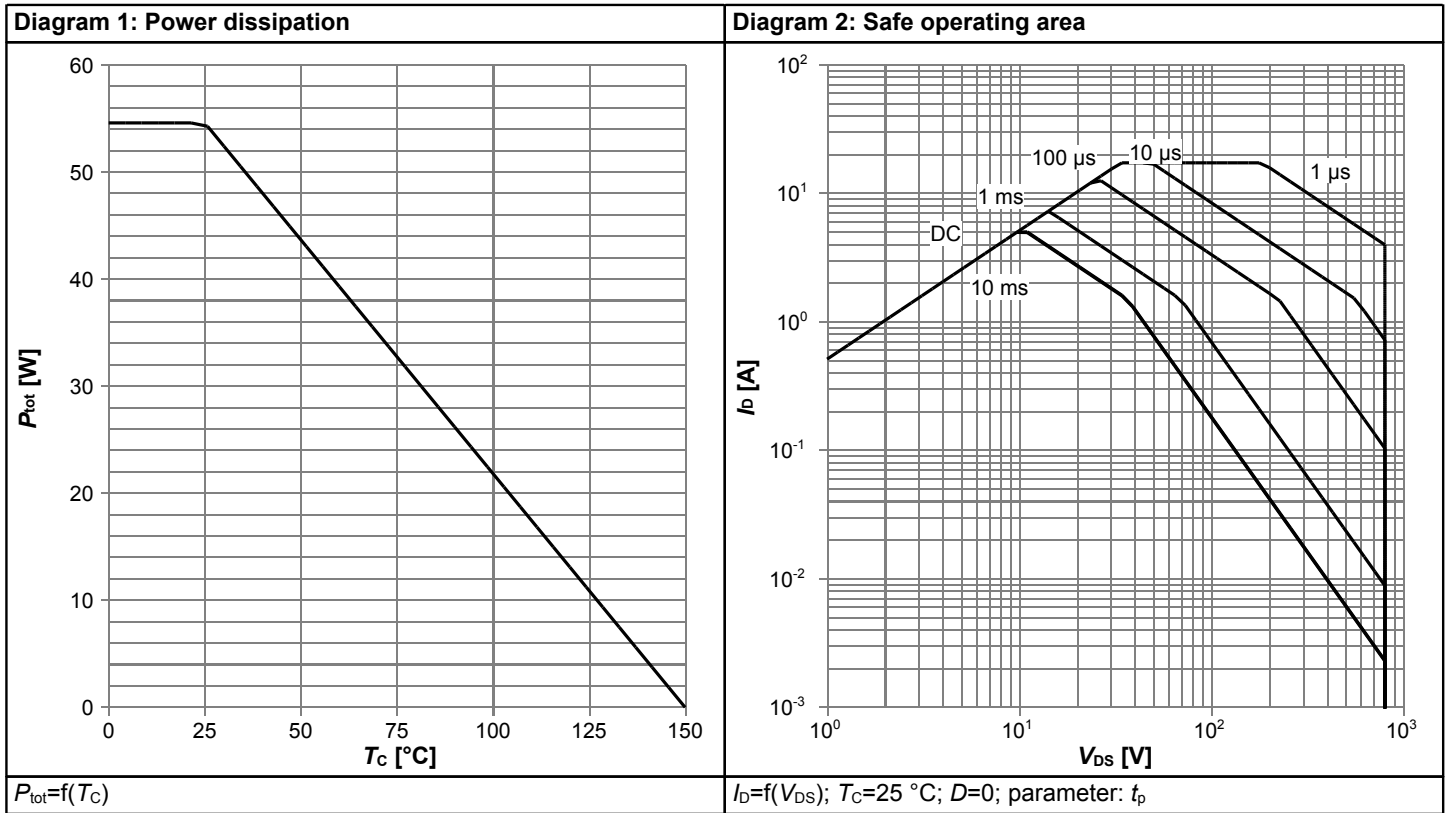
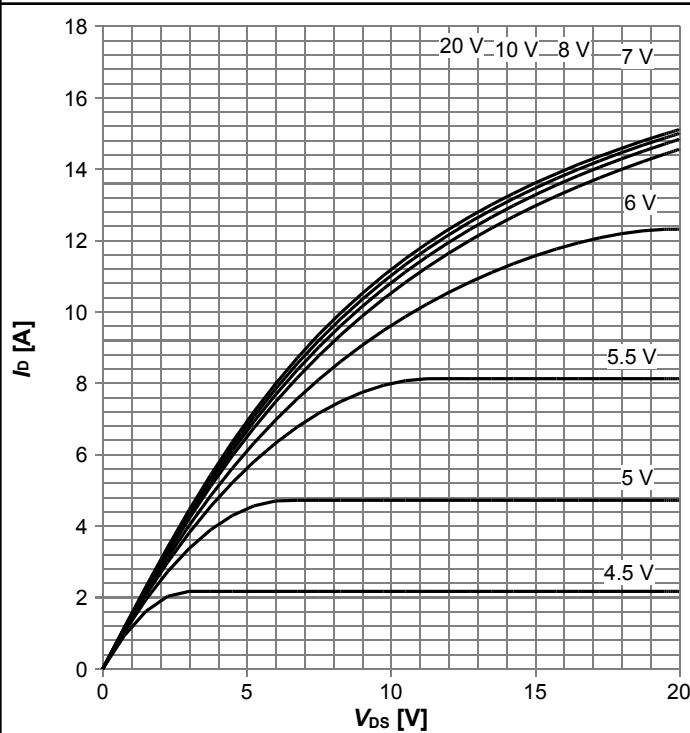
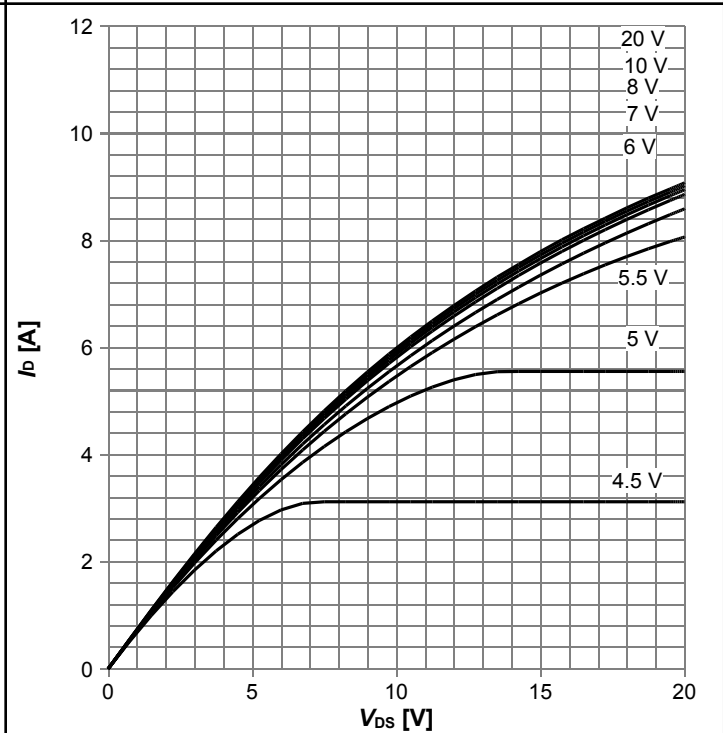


Diagram 5: Typ. output characteristics



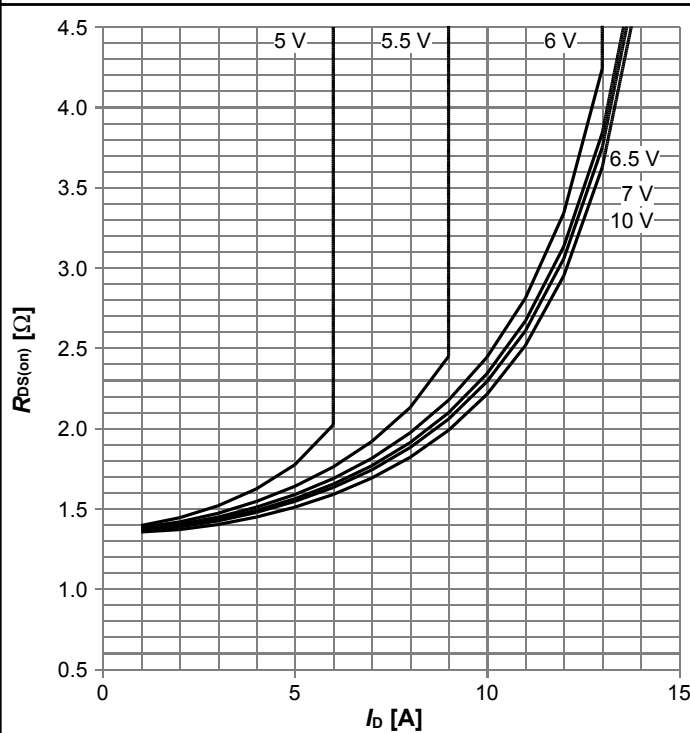
$I_D = f(V_{DS})$ ;  $T_j = 25^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 6: Typ. output characteristics



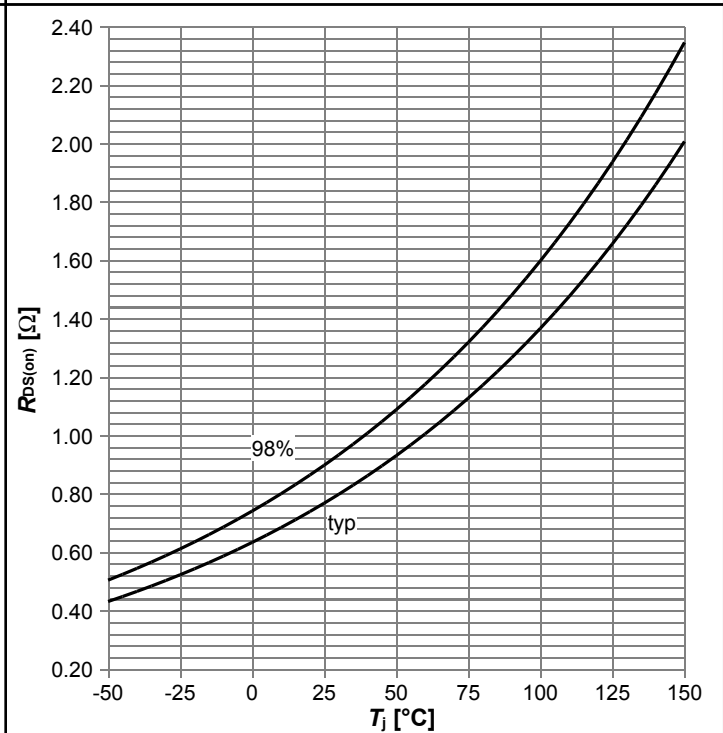
$I_D = f(V_{DS})$ ;  $T_j = 125^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 7: Typ. drain-source on-state resistance



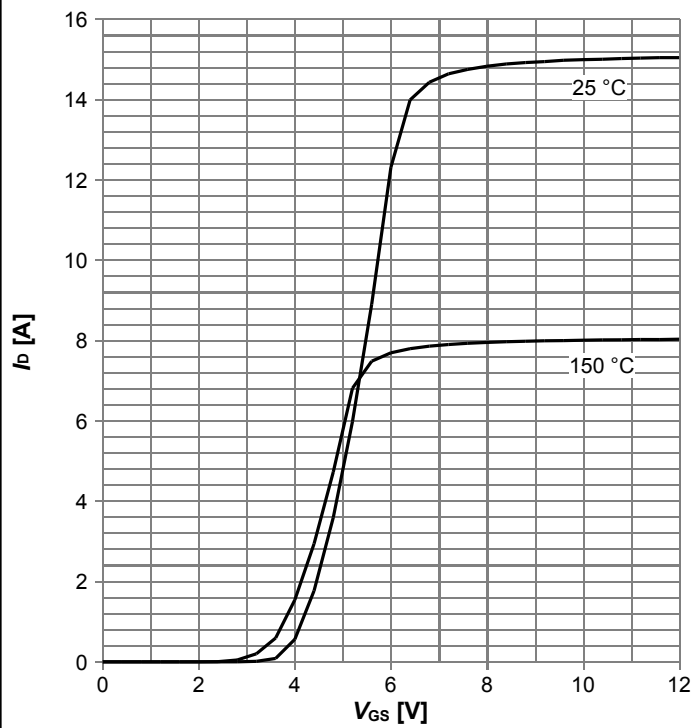
$R_{DS(on)} = f(I_D)$ ;  $T_j = 125^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 8: Drain-source on-state resistance



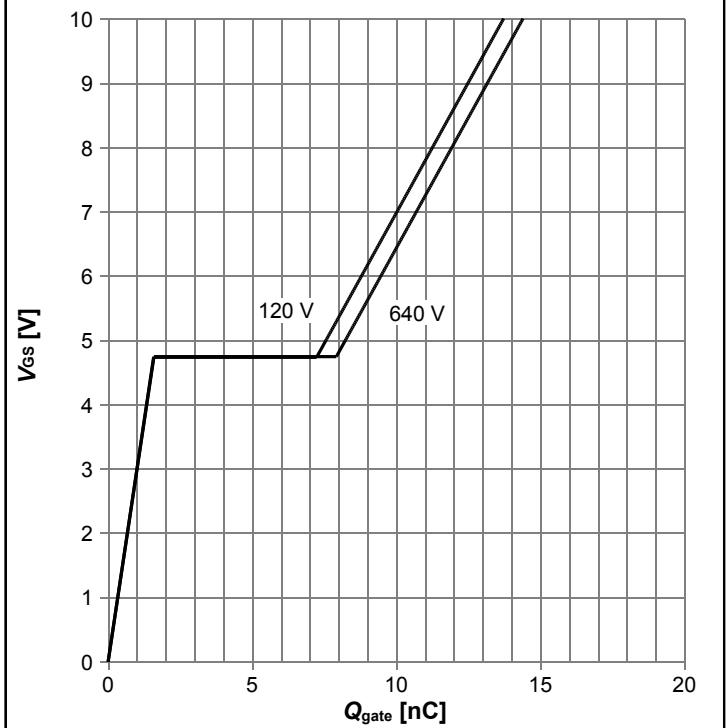
$R_{DS(on)} = f(T_j)$ ;  $I_D = 2.7\text{ A}$ ;  $V_{GS} = 10\text{ V}$

Diagram 9: Typ. transfer characteristics



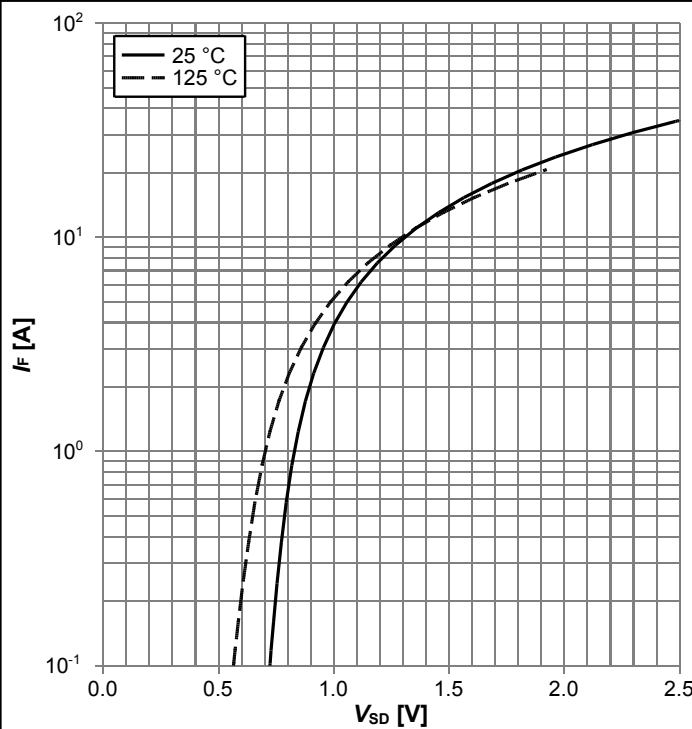
$I_D=f(V_{GS})$ ;  $V_{DS}=20V$ ; parameter:  $T_j$

Diagram 10: Typ. gate charge



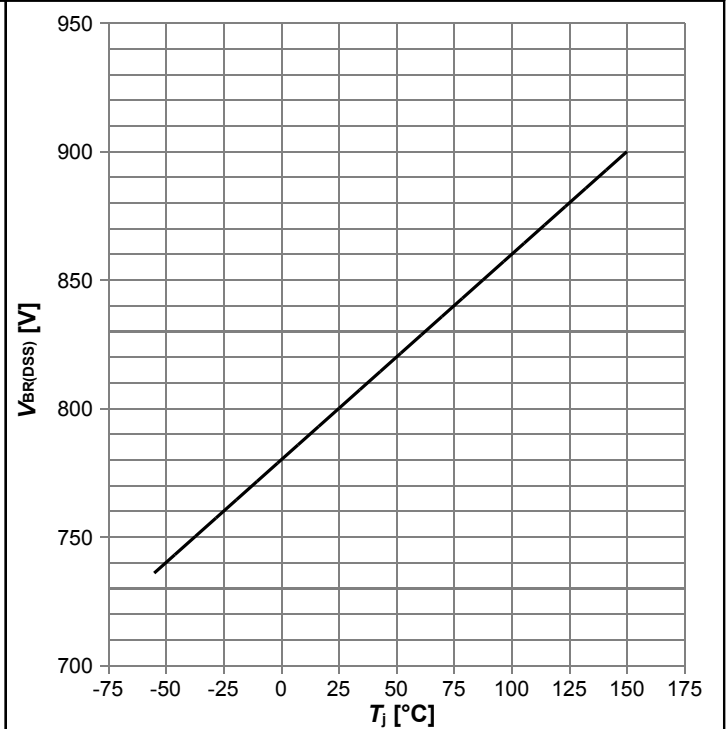
$V_{GS}=f(Q_{gate})$ ;  $I_D=2.2$  A pulsed; parameter:  $V_{DD}$

Diagram 11: Forward characteristics of reverse diode



$I_F=f(V_{SD})$ ; parameter:  $T_j$

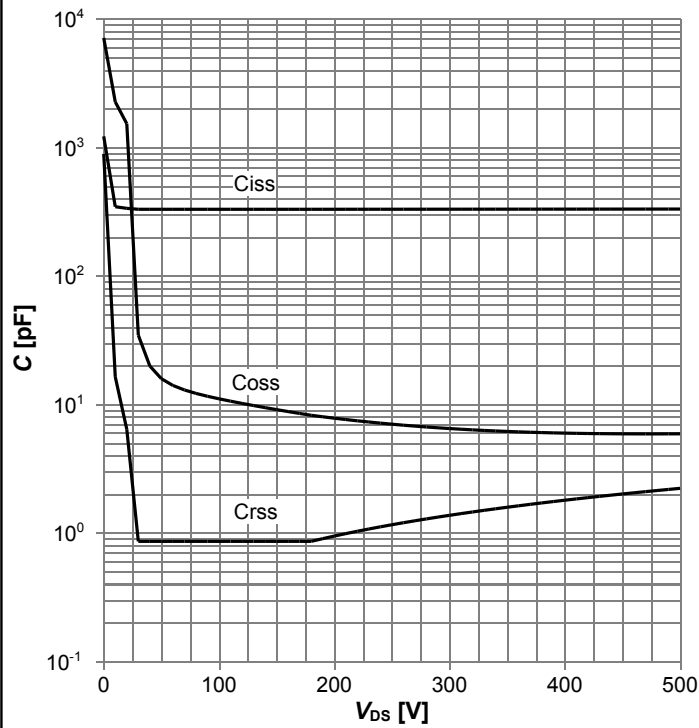
Diagram 13: Drain-source breakdown voltage



$V_{BR(DSS)}=f(T_j)$ ;  $I_D=1$  mA

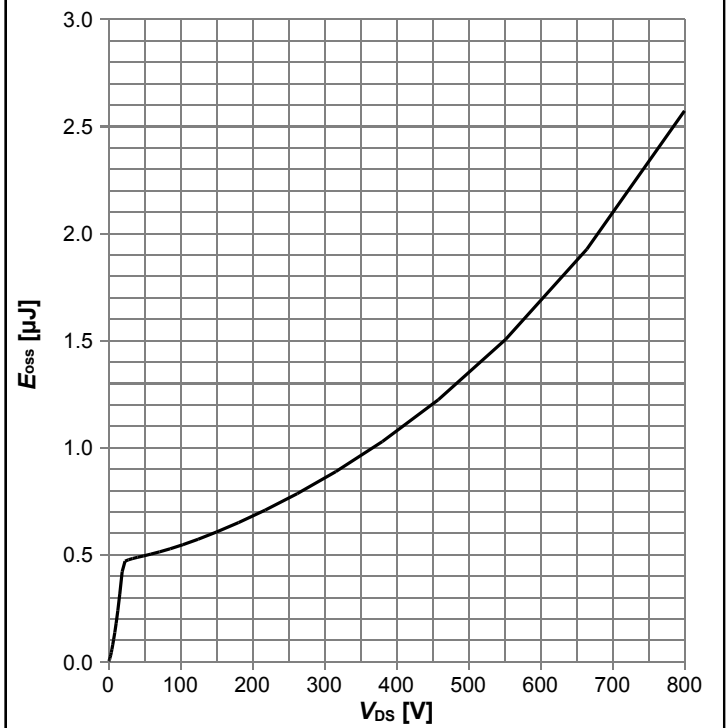


Diagram 14: Typ. capacitances



$C=f(V_{DS}); V_{GS}=0\text{ V}; f=250\text{ kHz}$

Diagram 15: Typ. Coss stored energy



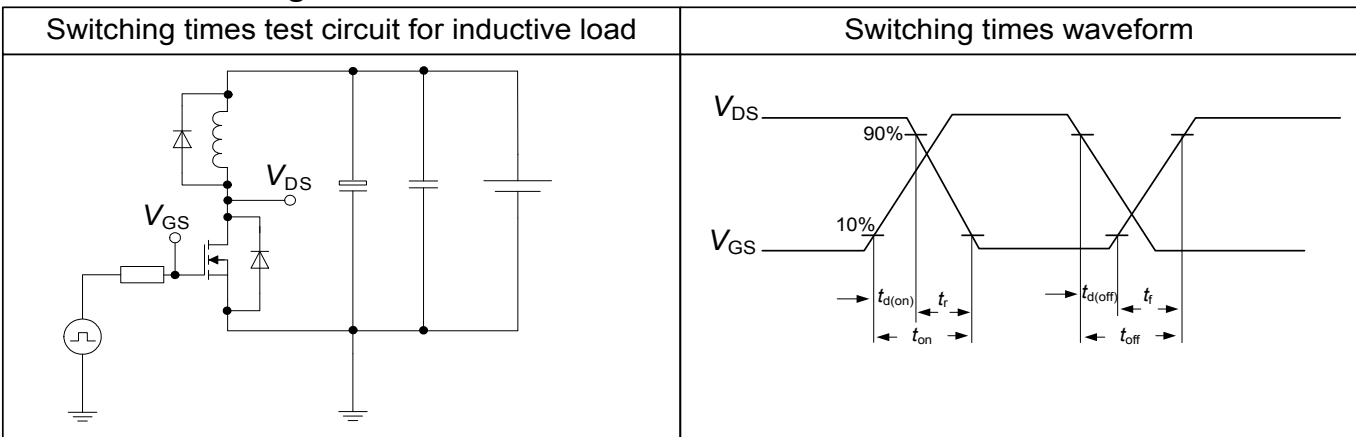
$E_{oss}=f(V_{DS})$

## 5 Test Circuits

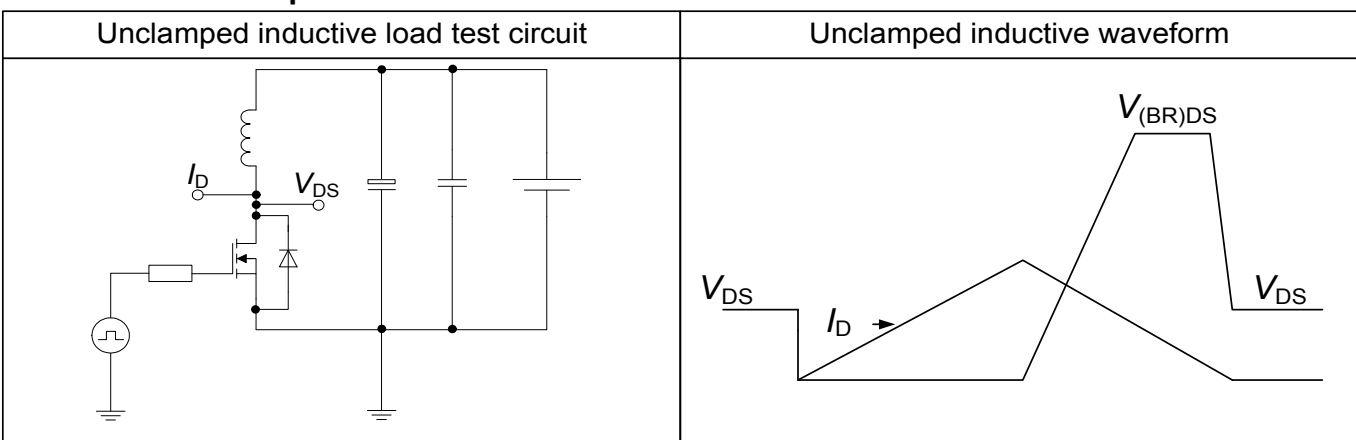
**Table 8 Diode characteristics**



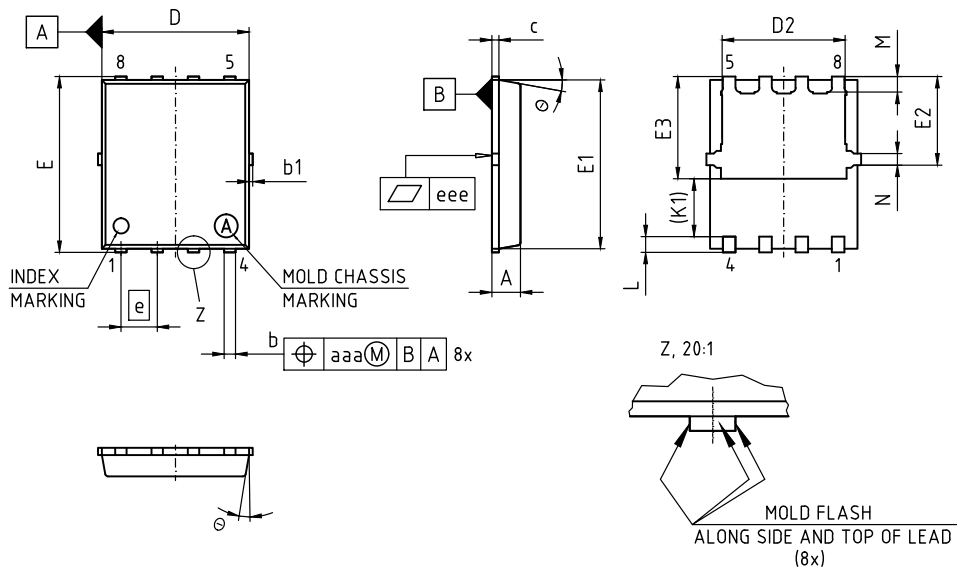
**Table 9 Switching times**



**Table 10 Unclamped inductive load**



## 6 Package Outlines



DIMENSION b DOES NOT INCLUDE MOLD FLASH  
AT PACKAGE SIDE NEAR DIMENSION b1:  
REMOVAL OF MOLD GATE.  
INTRUSION 0.1 MAX.  
PROTRUSION 0.1 MAX.  
ALL METAL SURFACES ARE PLATED; EXCEPT AREA OF CUT

DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	0.90	1.10
b	0.30	0.50
b1	0.03	0.23
c	0.15	0.35
D	4.95	5.35
D2	4.20	4.40
E	6.02	6.42
E1	5.70	6.10
E2	3.04	3.24
E3	3.52	3.72
e	1.27	
K1	(2.02)	
L	0.49	0.69
M	0.49	0.69
N	0.30	0.50
ϕ	8.5°	11.5°
aaa	0.25	
eee	0.05	

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Figure 1 Outline ThinPAK 5x6 SMD, dimensions in mm

## 7 Appendix A

### Table 11 Related Links

- IFX CoolMOS Webpage: [www.infineon.com](http://www.infineon.com)
- IFX Design tools: [www.infineon.com](http://www.infineon.com)

## Revision History

IPLK80R900P7

**Revision: 2021-07-23, Rev. 2.1**

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2020-07-17	Release of final version
2.1	2021-07-23	Update of maximum Operation temperature

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